TECHNICAL DATA DATA SHEET 4511, REV. -

POWER SCHOTTKY RECTIFIER Low Reverse Leakage

Applications:

• Switching Power Supply • Converters • Free-Wheeling Diodes • Polarity Protection Diode

Features:

- Ultra Low Reverse Leakage Current
- Soft Reverse Recovery at Low and High Temperature
- Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	100	V
Max. Average Forward	I _{F(AV)}	50% duty cycle, rectangular	30	Α
Current		wave form		
Max. Peak One Cycle Non-	I _{FSM}	8.3 ms, half Sine wave	570	Α
Repetitive Surge Current		(per leg)		
Non-Repetitive Avalanche	E _{AS}	$T_J = 25 ^{\circ}\text{C}, I_{AS} = 1.3 \text{A},$	27	mJ
Energy		L = 40mH (per leg)		
Repetitive Avalanche	I _{AR}	I _{AS} decay linearly to 0 in 1 μs	1.3	Α
Current		f limited by T _J max V _A =1.5V _R		
Thermal Resistance	R_{thJC}	Per Package	0.50	°C/W
Max. Junction Temperature	T _J	-	-65 to +200	°C
Max. Storage Temperature	T _{stg}	-	-65 to +200	°C

Electrical Characteristics:

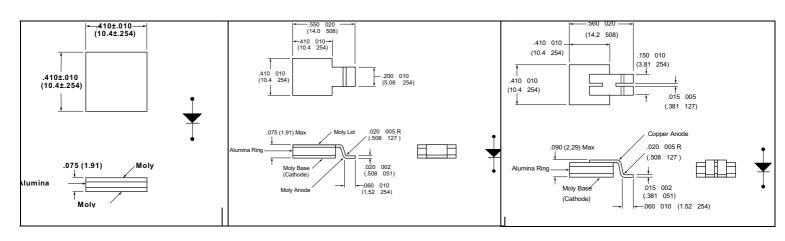
Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V_{F1}	@ 30A, Pulse, T _J = 25 °C	0.84	V
		(per leg) measured at the leads		
	V_{F2}	@ 30A, Pulse, T _J = 125 °C	0.68	V
		(per leg) measured at the leads		
Max. Reverse Current	I _{R1}	@V _R = 100V, Pulse,	0.02	mA
		$T_J = 25 ^{\circ}\text{C} \text{ (per leg)}$		
	I _{R2}	@V _R = 100V, Pulse,	2.0	mA
		T _J = 125 °C (per leg)		
Max. Junction Capacitance	C _T	$@V_R = 5 \text{ V}, T_C = 25 ^{\circ}\text{C}$	1000	pF
		$f_{SIG} = 1 MHz,$		
		$V_{SIG} = 50 \text{mV (p-p) (per leg)}$		

Due to the nature of the 100V Schottky devices, some degradation in t_{rr} performance at high temperatures should be expected, unlike conventional lower voltage Schottkys.

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Vf Curves shown are for die only.

Mechanical Dimensions: in inches / mm



SHD-3A SHD-3B

Typical Forward Characteristics Typical Reverse Characteristics 10² 200 ℃ 10¹ 175℃ Instantaneous Reverse Current - I_R (mA) 150℃ 10⁰ 125℃ 200℃ 10¹ 10⁻¹ 100℃ 175℃ nstantaneous Forward Current - I_F (A) 75℃ 10⁻² **50**℃ 10⁻³ 10⁰ 25℃ 10⁻⁴ 125℃ 0 20 100 120 40 60 Reverse Voltage - V_R (V) **Typical Junction Capacitance** 25℃ 900 Junction Capacitance - C_T (pF) 10⁻¹ 800 700 600 500 25℃ 400 300 200 10⁻² 100 0.2 0.8 0.3 0.4 0.5 0.6 0.7 0 20 100 40 60 120 Forward Voltage Drop - V_F (V) Reverse Voltage - V_R (V)

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TECHNICAL DATA

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